

## ABSTRACT OF THE DISCLOSURE

A ferroelectric film is formed by an oxide that is described by a general formula  $AB_{1-x}Nb_xO_3$ . An A element includes at least Pb, and a B element includes at least one  
5 of Zr, Ti, V, W, Hf and Ta. The ferroelectric film includes Nb within the range of:  $0.05 \leq x < 1$ . The ferroelectric film can be used for any of ferroelectric memories of 1T1C, 2T2C and simple matrix types.